

Pranab Biswas

List of Publications by Year in descending order

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28
papers

436
citations

840776

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713466

21
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28
all docs

28
docs citations

28
times ranked

728
citing authors

#	ARTICLE	IF	CITATIONS
1	Understanding the efficacy of Cu in creating oxygen vacancies and temperature dependent electrical transport in solution processed Cu:ZnO thin films. <i>Materials Science in Semiconductor Processing</i> , 2020, 120, 105311.	4.0	8
2	Efficient Resistive Switching and Spike Rate Dependent Plasticity in a New CuCrO_2 Memristor for Plausible Neuromorphic Systems. <i>IEEE Transactions on Electron Devices</i> , 2020, 67, 3451-3458.	3.0	10
3	Tuning of oxygen vacancy-induced electrical conductivity in Ti-doped hematite films and its impact on photoelectrochemical water splitting. <i>Scientific Reports</i> , 2020, 10, 7463.	3.3	28
4	Solution-processed n-ZnO nanorod/p-Co ₃ O ₄ nanoplate heterojunction light-emitting diode. <i>Applied Surface Science</i> , 2017, 406, 192-198.	6.1	46
5	Improved UV response of ZnO nanotubes by resonant coupling of anchored plasmonic silver nanoparticles. <i>Nanotechnology</i> , 2017, 28, 225502.	2.6	18
6	Enhanced photoluminescence in electrodeposited NiO nanowalls mediated by plasmonic Au nanoparticle. <i>Materials Chemistry and Physics</i> , 2017, 201, 63-68.	4.0	8
7	Oxygen vacancy-induced red light emission from flexible inorganic micropatterned p-CuO/n-ZnO heterojunction light-emitting diode. <i>Applied Physics Letters</i> , 2016, 109, .	3.3	14
8	Device characteristics of amorphous indium-gallium-zinc-oxide channel capped with silicon oxide passivation layers. <i>Materials Science in Semiconductor Processing</i> , 2016, 49, 34-39.	4.0	9
9	Adopting Novel Strategies in Achieving High-Performance Single-Layer Network Structured ZnO Nanorods Thin Film Transistors. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 11564-11574.	8.0	11
10	Low-Temperature Facile Synthesis of Sb-Doped p-Type ZnO Nanodisks and Its Application in Homo Junction Light-Emitting Diode. <i>ACS Applied Materials & Interfaces</i> , 2016, 8, 13018-13026.	8.0	58
11	Low temperature solution process-based defect-induced orange-red light emitting diode. <i>Scientific Reports</i> , 2015, 5, 17961.	3.3	13
12	Direct Transfer Printing with Metal Oxide Layers for Fabricating Flexible Nanowire Devices. <i>Advanced Functional Materials</i> , 2015, 25, 6921-6926.	14.9	10
13	An alternative approach to investigate the origin of p-type conductivity in arsenic doped ZnO. <i>Current Applied Physics</i> , 2015, 15, 1256-1261.	2.4	13
14	Lead-free epitaxial ferroelectric material integration on semiconducting (100) Nb-doped SrTiO ₃ for low-power non-volatile memory and efficient ultraviolet ray detection. <i>Scientific Reports</i> , 2015, 5, 12415.	3.3	42
15	InAs quantum dots as charge storing elements for applications in flash memory devices. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2015, 198, 102-107.	3.5	5
16	Fabrication and characterization of p-Si/n-ZnO heterojunction ultraviolet photodetector. <i>AIP Conference Proceedings</i> , 2015, .	0.4	0
17	Photovoltaic conversion of visible spectrum by GaP capped InP quantum dots grown on Si (100) by metalorganic chemical vapor deposition. <i>Applied Physics Letters</i> , 2015, 106, 012103.	3.3	0
18	Au/p-Si Schottky junction solar cell: Effect of barrier height modification by InP quantum dots. <i>Solar Energy Materials and Solar Cells</i> , 2015, 132, 230-236.	6.2	39

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19	Photoluminescence study based prediction on visible luminescence from n-Zno/p-GaAs heterojunction. , 2014, , .		0
20	Effect of band alignment on photoluminescence and carrier escape from InP surface quantum dots grown by metalorganic chemical vapor deposition on Si. Journal of Applied Physics, 2014, 115, 043101.	2.5	2
21	Anomalous diffusion of Ga and As from semi-insulating GaAs substrate into MOCVD grown ZnO films as a function of annealing temperature and its effect on charge compensation. AIP Advances, 2014, 4, 057108.	1.3	4
22	Effect of band offset on carrier transport and infrared detection in InP quantum dots/Si nano-heterojunction grown by metalorganic chemical vapor deposition technique. Journal of Applied Physics, 2014, 115, .	2.5	11
23	Fabrication of n-ZnO/p-GaAs Heterojunction and Prediction of Its Luminescence Based on Photoluminescence Study. Environmental Science and Engineering, 2014, , 815-818.	0.2	0
24	Varying Photoconductivity of ZnO as a Function of Annealing Temperature. Environmental Science and Engineering, 2014, , 819-821.	0.2	1
25	Super rapid response of humidity sensor based on MOCVD grown ZnO nanotips array. Sensors and Actuators B: Chemical, 2013, 178, 331-338.	7.8	55
26	GaAs metal-oxide-semiconductor based nonvolatile memory devices embedded with ZnO quantum dots. Journal of Applied Physics, 2013, 114, 084509.	2.5	10
27	A study on electrical transport vis-À-vis the effect of thermal annealing on the p-type conductivity in arsenic-doped MOCVD grown ZnO in the temperature range 10â€“300K. Journal of Alloys and Compounds, 2013, 552, 304-309.	5.5	11
28	Charge storage properties of InP quantum dots in GaAs metal-oxide-semiconductor based nonvolatile flash memory devices. Applied Physics Letters, 2012, 101, 212108.	3.3	10